Silicon Epitaxial Planar Diode

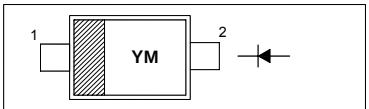
High Voltage Switching Diode

Features

- Fast switching speed
- High conductance
- High reverse breakdown voltage rating

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**YM**"
Simplified outline SOD-323 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	400	V
Reverse Voltage	V_R	350	V
Continuous Forward Current	I_F	225	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current (1 ms)	I_{FSM}	2	A
Power Dissipation	P_d	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 20 mA at I_F = 100 mA at I_F = 200 mA	V_F	 - - -	 0.87 1 1.25	V
Reverse Current at V_R = 240 V	I_R	-	100	nA
Reverse Breakdown Voltage at I_R = 150 µA	$V_{(BR)R}$	400	-	V
Total Capacitance at V_R = 0 , f = 1 MHz	C_T	-	5	pF
Reverse Recovery Time at I_F = I_R = 30 mA , i_{rr} = 3 mA, R_L = 100 Ω	t_{rr}	-	100	ns

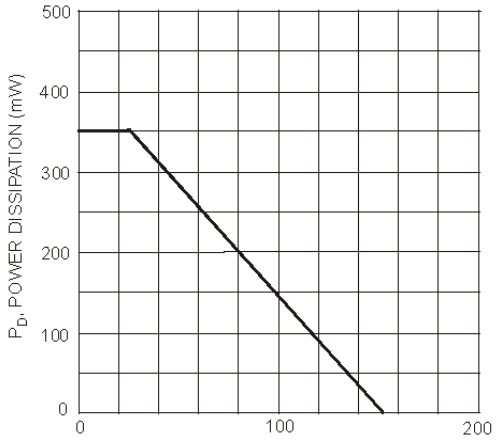


Fig. 1 Power Derating Curve, Total Package

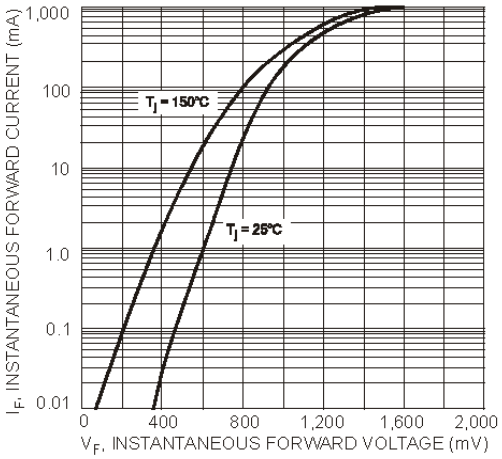


Fig. 2 Typical Forward Characteristics, Per Element

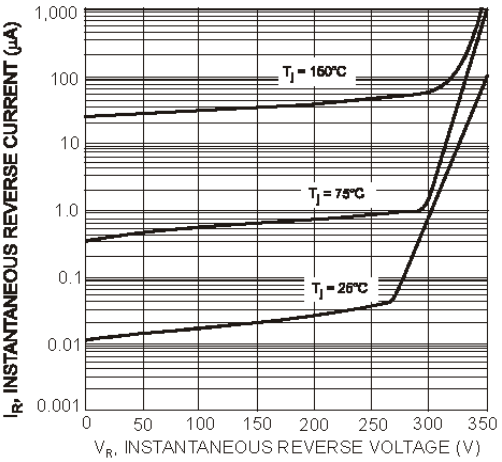


Fig. 3 Typical Reverse Characteristics, Per Element

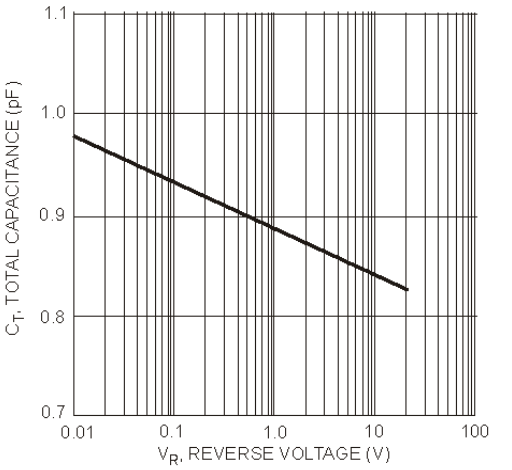


Fig. 4 Total Capacitance vs. Reverse Voltage, Per Element